Inventor:

Neal R. Rueger et al.

Title:

Methods of Filling Gaps and Methods of Depositing Materials Using High

Density Plasma Chemical Vapor Deposition

Assignee:

Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

References – See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. No admission is made regarding whether any of the submitted references is prior art. Copies of any foreign patent documents and non-patent literature are attached.

Respectfully submitted,

Dated: September 23, 2003 Attorney:

Form PTO-1449)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			ATTY. DOCKET N MI22-2145		SERIAL NO. Not yet assigned		
					APPLICANT Neal R. Rueger et a				
		(FILING DATE Filed herewith			GROUP Not yet assigned		
				U.S. PATENT DOCUMENTS		·			
*Examiner Initial		Document Number	Date	Name	Name		Subclass Filing Date If Appropriate		ate oriate
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